

TSC4505

High Voltage NPN Transistor



SOT-23

Pin Definition:

- 1. Base
- 2. Emitter
- Collector

PRODUCT SUMMARY

BV _{CEO}	400V
BV _{CBO}	400V
Ic	300mA
V _{CE(SAT)}	$0.1V @ I_C / I_B = 10mA / 1mA$

Ordering Information Features

Part No.	Package	Packing
TSC4505CX RF	SOT-23	3Kpcs / 7" Reel
TSC4505CX RFG	SOT-23	3Kpcs / 7" Reel

Note: "G" denotes Halogen Free Product.

- Low $V_{CE(SAT)} 0.15V @ I_C / I_B = 10mA / 10mA (Typ.)$
- Complementary part with TSA1759

Structure

- Epitaxial Planar Type
- NPN Silicon Transistor

Absolute Maximum Rating (T_A = 25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit	
Collector-Base Voltage		$V_{\sf CBO}$	400	V
Collector-Emitter Voltage		V_{CEO}	400	V
Emitter-Base Voltage		V_{EBO}	6	V
Collector Current		I _C	300	mA
Collector Power Dissipation	SOT-23	P_{D}	0.225	W
Operating Junction Temperature		T_J	+150	°C
Operating Junction and Storage Temperature Ran	T_{STG}	- 55 to +150	°C	

Note: Single pulse, Pw=20ms, Duty≤50%

Electrical Specifications (T_A = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Collector-Base Breakdown Voltage	$I_C = 50uA, I_E = 0$	BV_CBO	400		1	V
Collector-Emitter Breakdown Voltage	$I_C = 1 \text{mA}, I_B = 0$	BV _{CEO}	400		1	V
Emitter-Base Breakdown Voltage	$I_E = 50uA, I_C = 0$	BV_{EBO}	6		1	V
Collector Cutoff Current	$V_{CB} = 400V, I_{E} = 0$	I _{CBO}			10	uA
Collector-Emitter Reverse Current	$V_{CE} = 300V, R_{EB} = 4k\Omega$	I _{CER}	1		20	nA
Emitter Cutoff Current	$V_{EB} = 6V, I_{C} = 0$	I _{EBO}	ŀ		10	uA
Collector-Emitter Saturation Voltage	$I_C / I_B = 10mA / 1mA$	V _{CE(SAT)}		0.1	0.5	V
Base-Emitter Saturation Voltage	$I_C / I_B = 10mA / 1mA$	V _{BE(SAT)}	1		1.5	V
DC Current Transfer Ratio	$V_{CE} = 10V, I_{C} = 10mA$	h _{FE}	100		270	
Transition Frequency	V _{CE} =10V, I _C =-10mA, f=10MHz	f _T	ľ	20	ľ	MHz
Output Capacitance	$V_{CB} = 10V, I_{E} = 0, f=1MHz$	Cob		7		pF





Pb RoHS COMPLIANCE

Electrical Characteristics Curve (T_A = 25°C, unless otherwise noted)

Figure 1. DC Current Gain

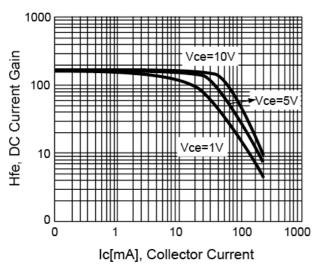


Figure 3. V_{BE(SAT)} v.s. Ic

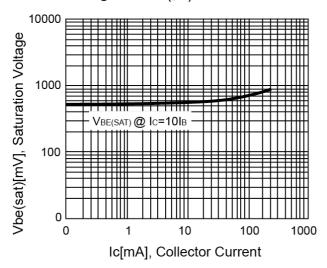


Figure 2. V_{CE(SAT)} v.s. Ic

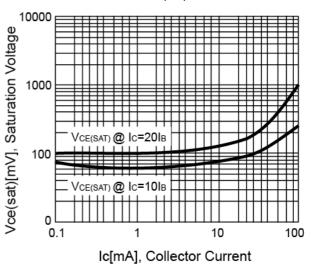
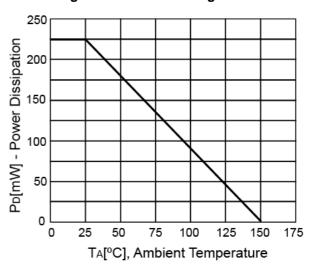


Figure 4. Power Derating Curve

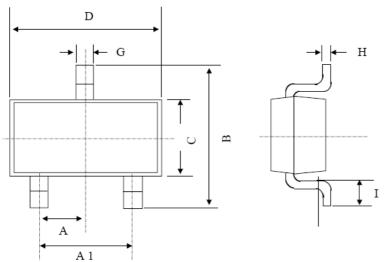




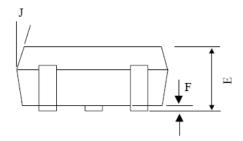


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SOT-23 Mechanical Drawing



SOT-23 DIMENSION						
DIM	MILLIM	MILLIMETERS		INCHES		
DIIVI	MIN	MAX	MIN	MAX.		
Α	1.00	BSC	0.039 BSC			
A1	2.00	BSC	0.079 BSC			
В	2.10	2.75	0.083	0.108		
С	1.20	1.60	0.047	0.063		
D	2.80	3.04	0.110	0.120		
Е	0.89	1.30	0.035	0.051		
F	0.01	0.10	0.000	0.004		
G	0.30	0.50	0.012	0.020		
Н	0.08	0.18	0.003	0.007		
Ī	0.30	0.60	0.012	0.024		





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